SCHOTTKY BARRIER RECTIFIER

BYM26 series

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack
- Also available with preformed leads for easy insertion.

DESCRIPTION

Rugged glass SOD64 package, using a high temperature alloyed construction. This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

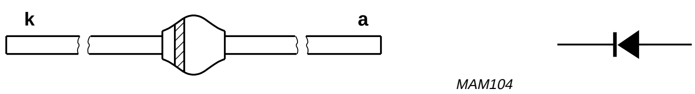

Fig.1 Simplified outline (SOD64) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage				
	BYM26A		–	200	V
	BYM26B		–	400	V
	BYM26C		–	600	V
	BYM26D		–	800	V
	BYM26E		–	1000	V
	BYM26F		–	1200	V
	BYM26G		–	1400	V
V_R	continuous reverse voltage				
	BYM26A		–	200	V
	BYM26B		–	400	V
	BYM26C		–	600	V
	BYM26D		–	800	V
	BYM26E		–	1000	V
	BYM26F		–	1200	V
	BYM26G		–	1400	V
$I_{F(AV)}$	average forward current	T_{tp} = 55 °C; lead length = 10 mm; see Figs 2 and 3; averaged over any 20 ms period; see also Figs 10 and 11			
	BYM26A to E		–	2.30	A
	BYM26F and G		–	2.40	A
$I_{F(AV)}$	average forward current	T_{amb} = 65 °C; PCB mounting (see Fig.19); see Figs 4 and 5; averaged over any 20 ms period; see also Figs 10 and 11			
	BYM26A to E		–	1.05	A
	BYM26F and G		–	1.00	A

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{FRM}	repetitive peak forward current	T_{tp} = 55 °C; see Figs 6 and 7			
	BYM26A to E		–	19	A
	BYM26F and G		–	21	A
I_{FRM}	repetitive peak forward current	T_{amb} = 65 °C; see Figs 8 and 9			
	BYM26A to E		–	8.0	A
	BYM26F and G		–	8.5	A
I_{FSM}	non-repetitive peak forward current	t = 10 ms half sine wave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	–	45	A
E_{RSM}	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j\,max}$ prior to surge; inductive load switched off	–	10	mJ
T_{stg}	storage temperature		–65	+175	°C
T_j	junction temperature	see Figs 12 and 13	–65	+175	°C

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage	I_F = 2 A; $T_j = T_{j\,max}$; see Figs 14 and 15				
	BYM26A to E		–	–	1.34	V
	BYM26F and G		–	–	1.34	V
V_F	forward voltage	I_F = 2 A; see Figs 14 and 15				
	BYM26A to E		–	–	2.65	V
	BYM26F and G		–	–	2.30	V
$V_{(BR)R}$	reverse avalanche breakdown voltage	I_R = 0.1 mA				
	BYM26A		300	–	–	V
	BYM26B		500	–	–	V
	BYM26C		700	–	–	V
	BYM26D		900	–	–	V
	BYM26E		1100	–	–	V
	BYM26F		1300	–	–	V
	BYM26G		1500	–	–	V
I_R	reverse current	$V_R = V_{RRMmax}$; see Fig.16	–	–	10	µA
		$V_R = V_{RRMmax}$; T_j = 165 °C; see Fig.16	–	–	150	µA
t_{rr}	reverse recovery time	when switched from I_F = 0.5 A to I_R = 1 A; measured at I_R = 0.25 A; see Fig.20				
	BYM26A to C		–	–	30	ns
	BYM26D and E		–	–	75	ns
	BYM26F and G		–	–	150	ns

BYM26 series

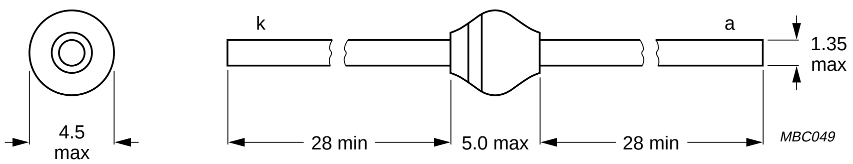
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C_d	diode capacitance	f = 1 MHz; V_R = 0 V; see Figs 17 and 18				
	BYM26A to C		–	85	–	pF
	BYM26D and E		–	75	–	pF
	BYM26F and G		–	65	–	pF
$\left\lvert\frac{dI_R}{dt}\right\rvert$	maximum slope of reverse recovery current	when switched from I_F = 1 A to $V_R \geq$ 30 V and dI_F/dt = −1 A/µs; see Fig.21				
	BYM26A to C		–	–	7	A/µs
	BYM26D and E		–	–	6	A/µs
	BYM26F and G		–	–	5	A/µs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point	lead length = 10 mm	25	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	75	K/W

Note

1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 µm, see Fig.19. For more information please refer to the *"General Part of associated Handbook".*

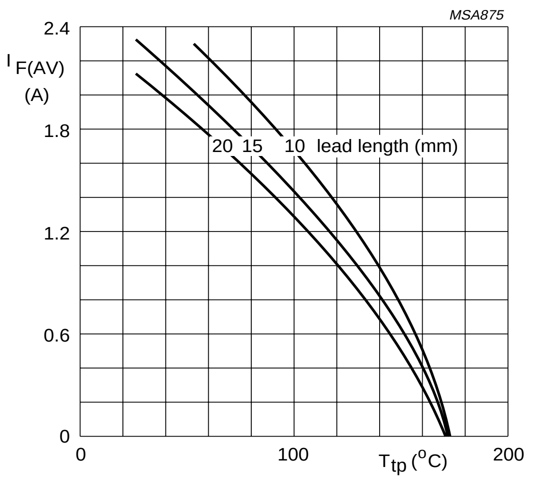


Dimensions in mm.
The marking band indicates the cathode.

Fig.22 SOD64.

BYM26 series

GRAPHICAL DATA

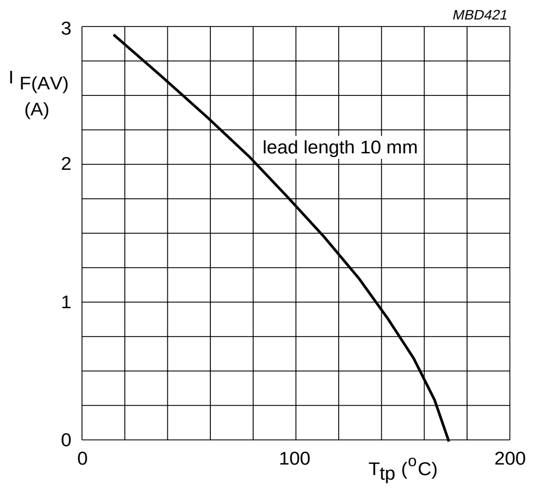


BYM26A to E

a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.

Switched mode application.

Fig.2 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).

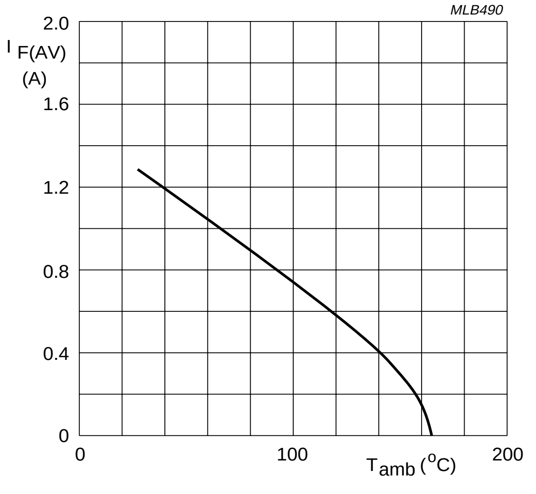


BYM26F and G

a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.

Switched mode application.

Fig.3 Maximum average forward current as a function of tie-point temperature (including losses due to reverse leakage).



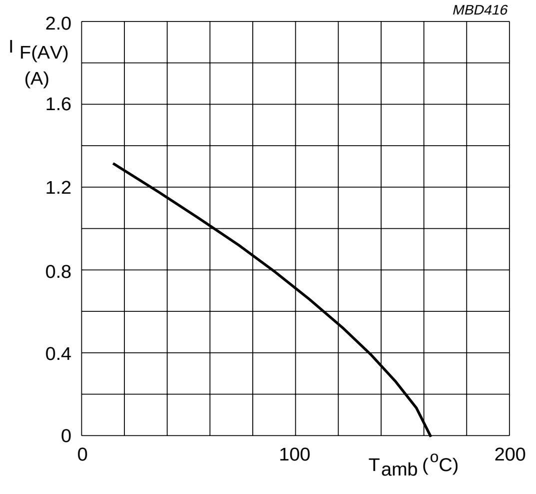
BYM26A to E

a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.

Device mounted as shown in Fig.19.

Switched mode application.

Fig.4 Maximum average forward current as a function of ambient temperature (including losses due to reverse leakage).



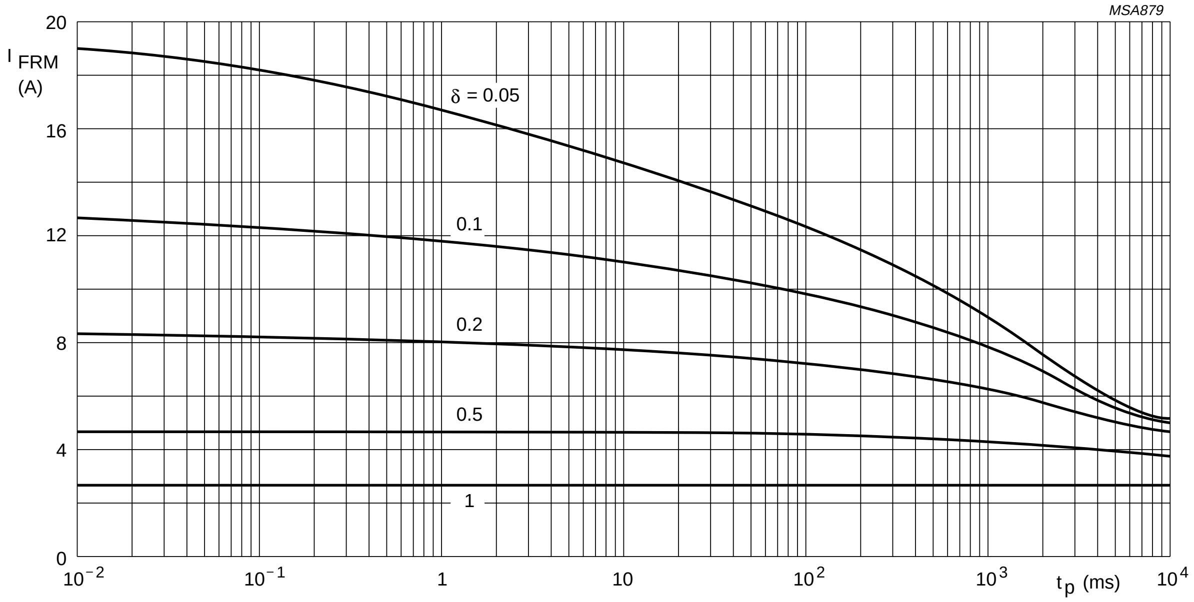
BYM26F and G

a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.

Device mounted as shown in Fig.19.

Switched mode application.

Fig.5 Maximum average forward current as a function of ambient temperature (including losses due to reverse leakage).

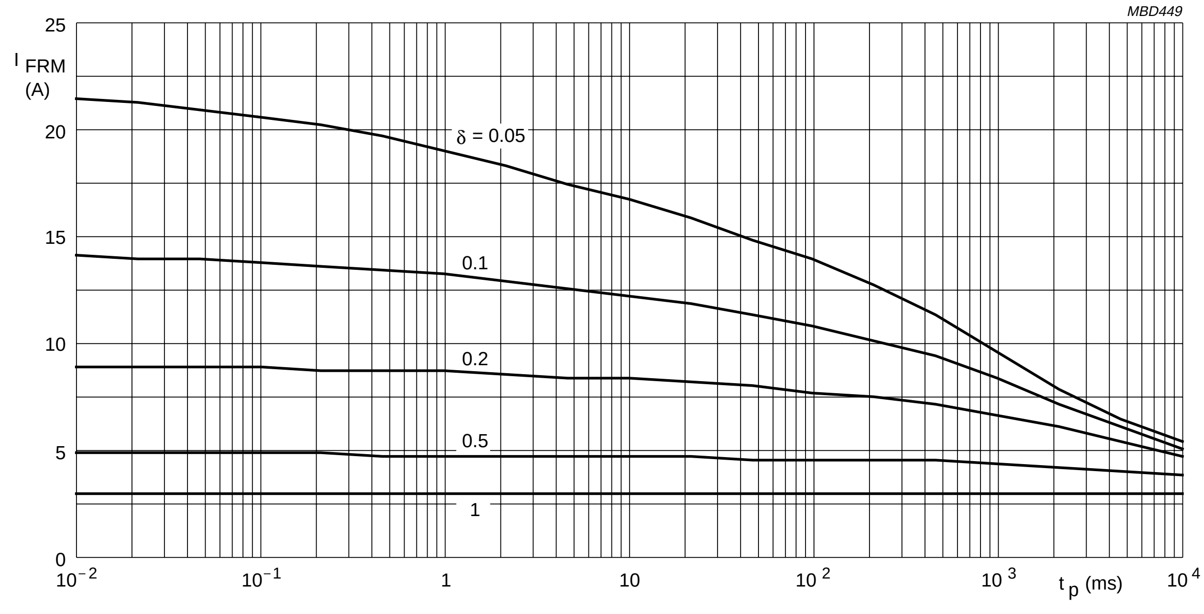


BYM26A to E

T_{tp} = 55°C; $R_{th\ j\text{-}tp}$ = 25 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

Fig.6 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

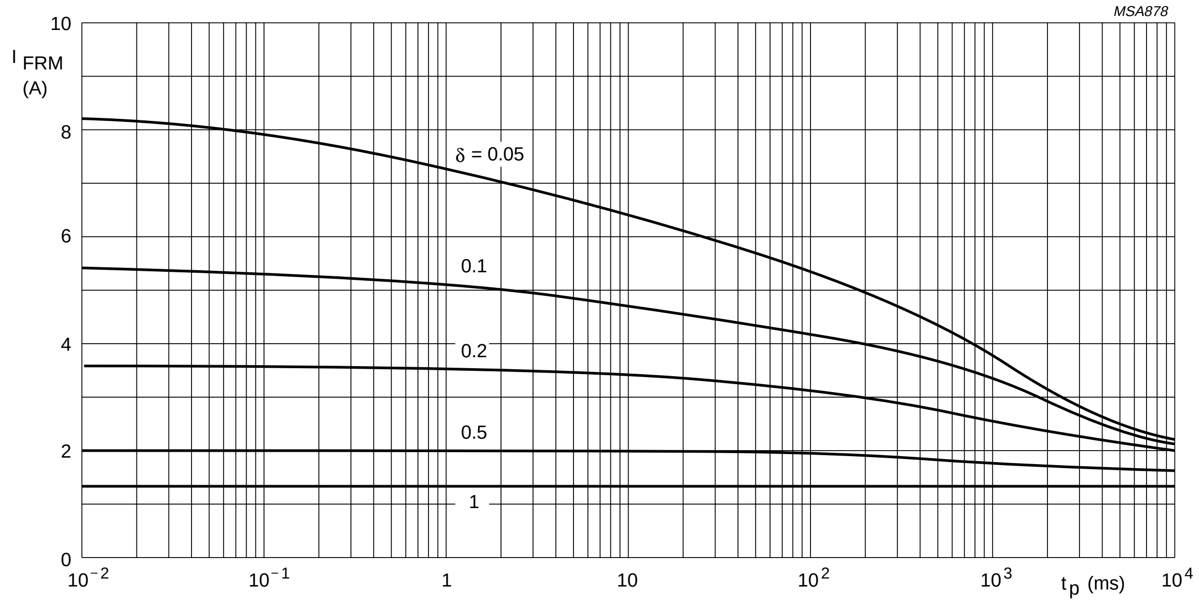


BYM26F and G

T_{tp} = 55°C; $R_{th\ j\text{-}tp}$ = 25 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 1400 V.

Fig.7 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

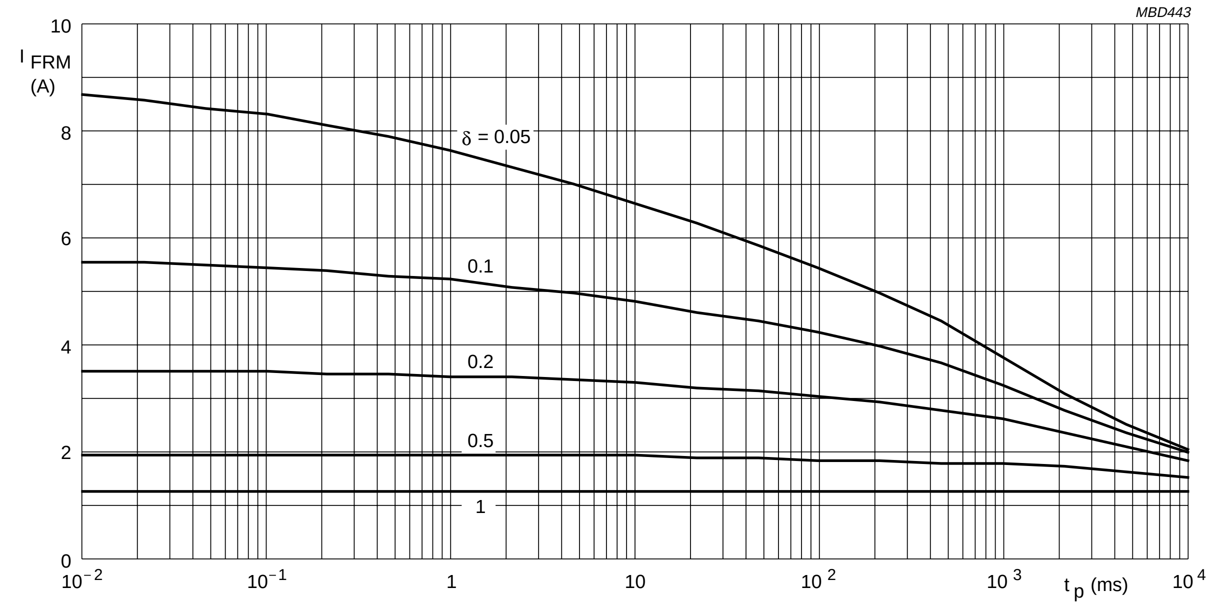


BYM26A to E

T_{amb} = 65 °C; $R_{th\ j\text{-}a}$ = 75 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 1000 V.

Fig.8 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.



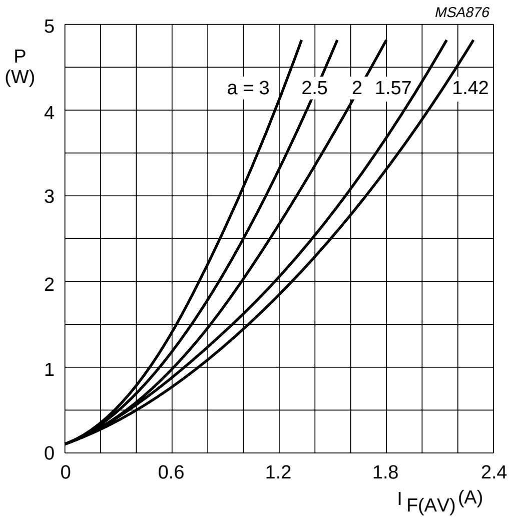
BYM26F and G

T_{amb} = 65 °C; $R_{th\ j\text{-}a}$ = 75 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 1400 V.

Fig.9 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

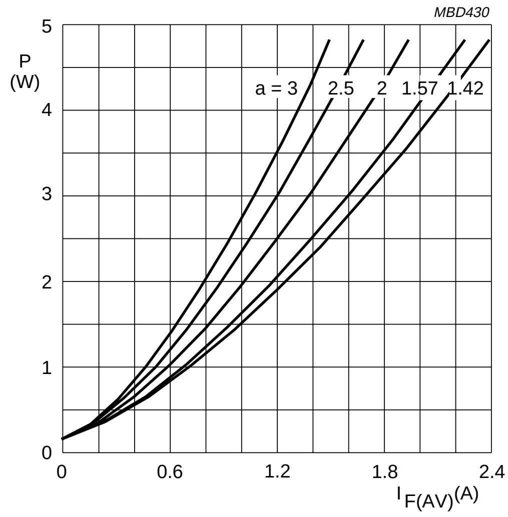
BYM26 series



BYM26A to E

a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; $\delta = 0.5$.

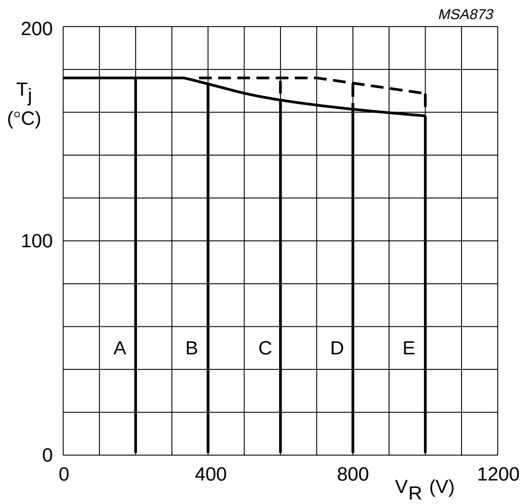
Fig.10 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



BYM26F and G

a = $I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; $\delta = 0.5$.

Fig.11 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.

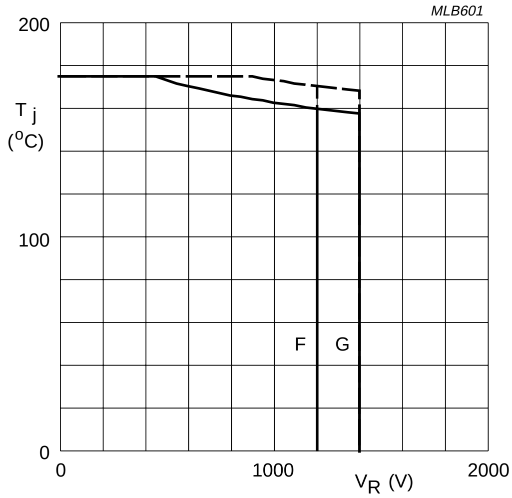


BYM26A to E

Solid line = V_R.

Dotted line = V_{RRM}; $\delta = 0.5$.

Fig.12 Maximum permissible junction temperature as a function of reverse voltage.

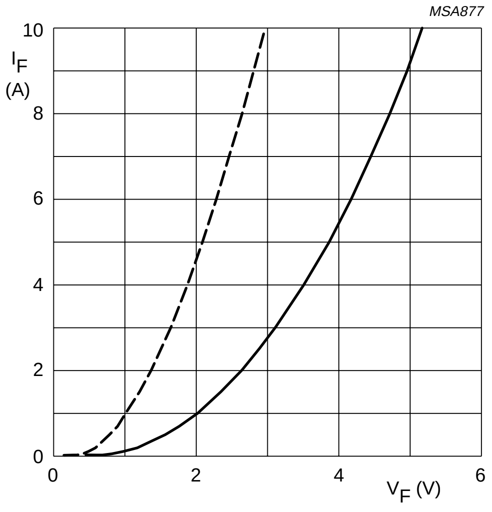


BYM26F and G

Solid line = V_R.

Dotted line = V_{RRM}; $\delta = 0.5$.

Fig.13 Maximum permissible junction temperature as a function of reverse voltage.

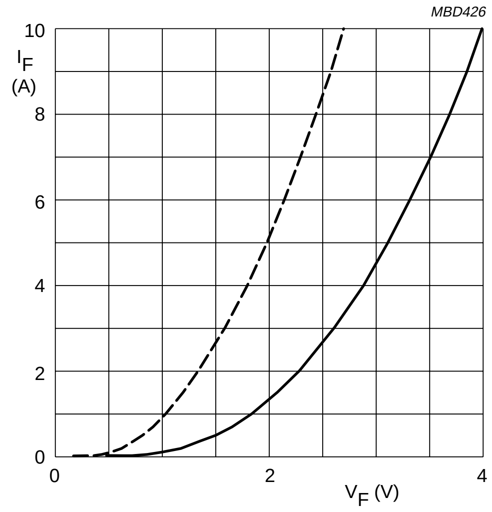


BYM26A to E

Dotted line: T_j = 175 °C.

Solid line: T_j = 25 °C.

Fig.14 Forward current as a function of forward voltage; maximum values.

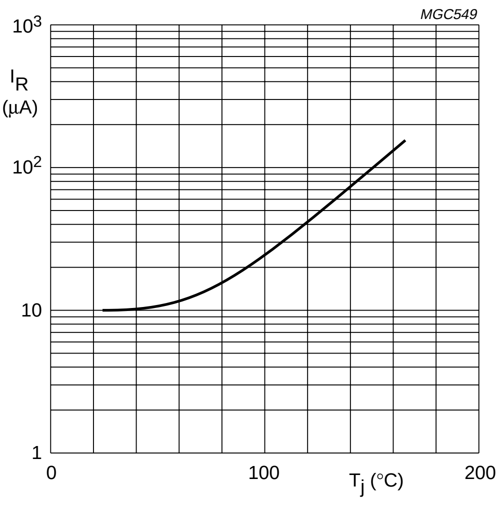


BYM26F and G

Dotted line: T_j = 175 °C.

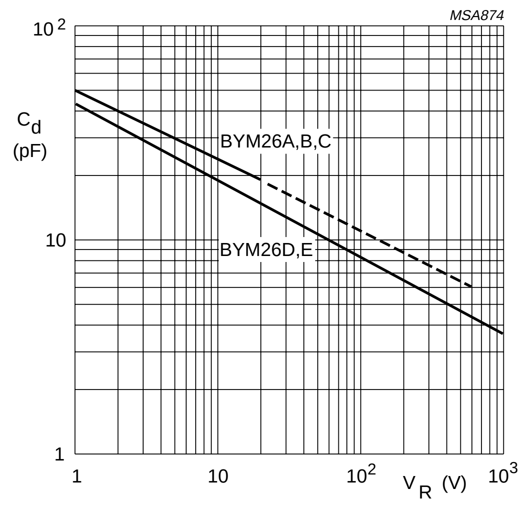
Solid line: T_j = 25 °C.

Fig.15 Forward current as a function of forward voltage; maximum values.



$V_R = V_{RRMmax}$.

Fig.16 Reverse current as a function of junction temperature; maximum values.

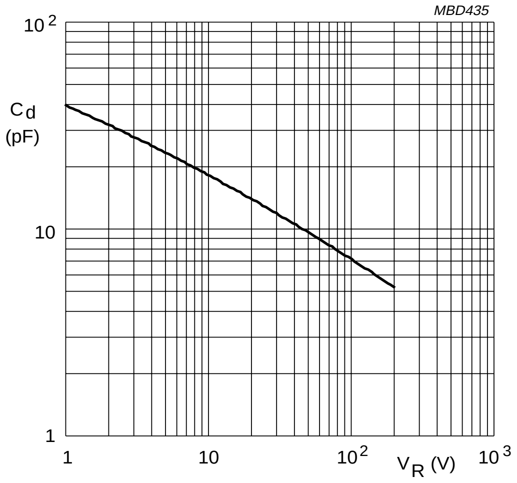


BYM26A to E

f = 1 MHz; T_j = 25 °C.

Fig.17 Diode capacitance as a function of reverse voltage; typical values.

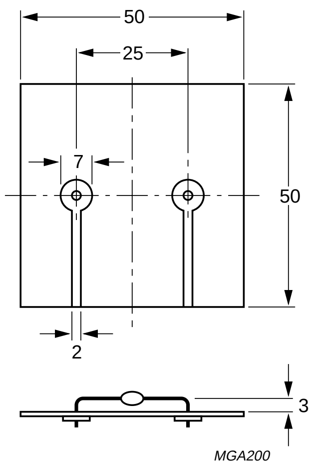
BYM26 series



BYM26F and G

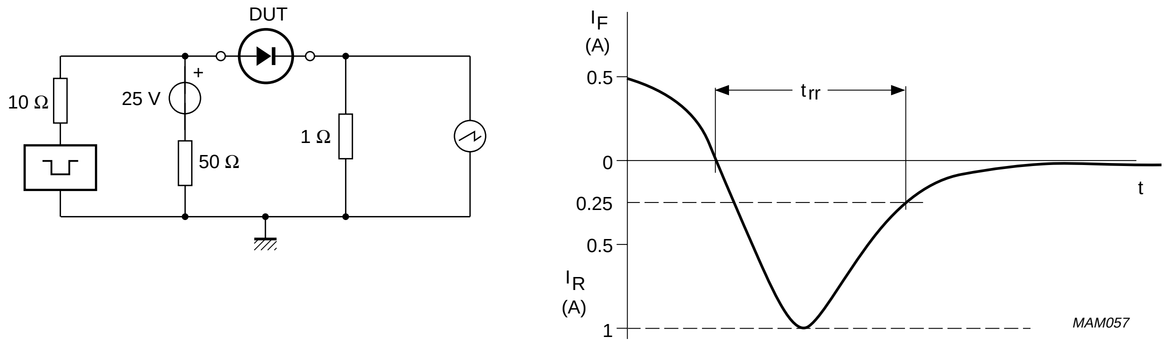
f = 1 MHz; T_j = 25 °C.

Fig.18 Diode capacitance as a function of reverse voltage; typical values.



Dimensions in mm.

Fig.19 Device mounted on a printed-circuit board.



Input impedance oscilloscope: 1 MΩ, 22 pF; $t_r \leq 7$ ns.

Source impedance: 50 Ω; $t_r \leq 15$ ns.

Fig.20 Test circuit and reverse recovery time waveform and definition.

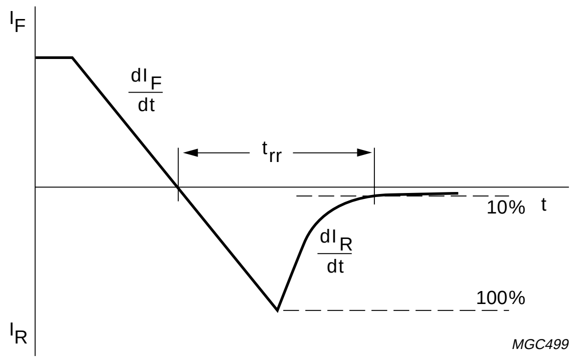


Fig.21 Reverse recovery definitions.